

Document No.	853-0106
ECN No.	86487
Date of Issue	November 11, 1986
Status	Product Specification
Memory Products	

82S115

4K-bit TTL bipolar PROM

DESCRIPTION

The 82S115 is field programmable and includes on-chip decoding and 2 chip enable inputs for ease of memory expansion. It features 3-State outputs for optimization of word expansion in bused organizations. A D-type latch is used to enable the 3-State output drivers. In the Transparent Read mode, stored data is addressed by applying a binary code to the address inputs while holding Strobe High. In this mode the bit drivers will be controlled solely by $\overline{CE1}$ and $\overline{CE2}$ lines.

In the Latched Read mode, outputs are held in their previous state (High, Low, or Hi-Z) as long as Strobe is Low, regardless of the state of Address or Chip Enable. A positive Strobe transition causes data from the applied address to reach the outputs if the chip is enabled, and causes outputs to go to the Hi-Z State if the chip is disabled.

A negative Strobe transition causes outputs to be locked into their last Read Data condition if the chip was enabled, or causes outputs to be locked into the Hi-Z condition if the chip was disabled.

Ordering information can be found on the following page.

This device is also processed to military requirements for operation over the military temperature range. For specifications and ordering information consult the Signetics Military Data Handbook.

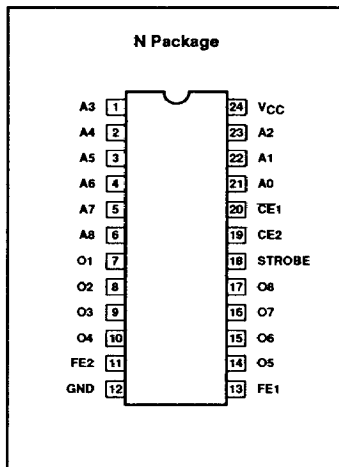
FEATURES

- Address access time: 60ns max
- Power dissipation: 165 μ A max
- Input loading: -100 μ A max
- Two Chip Enable inputs
- On-chip storage latches
- Schottky clamped
- Fully TTL compatible
- Outputs: 3-State

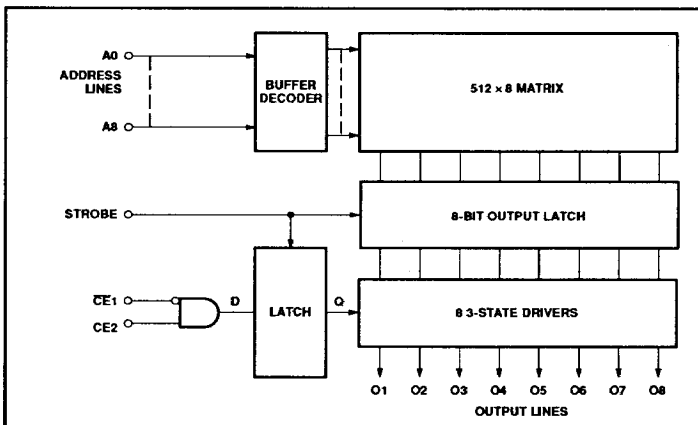
APPLICATIONS

- Microprogramming
- Hardware algorithms
- Character generation
- Control store
- Sequential controllers

PIN CONFIGURATION



BLOCK DIAGRAM



4K-bit TTL bipolar PROM (512 × 8)**82S115****ORDERING INFORMATION**

DESCRIPTION	ORDER CODE
24-Pin Plastic Dual-In-Line 600mil-wide	N82S115 N

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	RATING	UNIT
V _{CC}	Supply voltage	+7.0	V _{DC}
V _{IN}	Input voltage	+5.5	V _{DC}
T _{amb}	Operating temperature range	0 to +75	°C
T _{stg}	Storage temperature range	-65 to +150	°C

DC ELECTRICAL CHARACTERISTICS0°C ≤ T_{amb} ≤ +75°C, 4.75V ≤ V_{CC} ≤ 5.25V

SYMBOL	PARAMETER	TEST CONDITIONS ¹	LIMITS			UNIT
			Min	Typ ²	Max	
Input voltage						
V _{IL}	Low	I _{IN} = -12mA	2.0		0.8	V
V _{IH}	High					
V _{IC}	Clamp					
Output voltage						
V _{OL}	Low	CE1 = Low, CE2 = High I _{OUT} = 9.6mA I _{OUT} = -2.0mA	2.7	0.4	0.45	V
V _{OH}	High					
Input current¹						
I _{IL}	Low	V _{IN} = 0.45V			-100	μA
I _{IH}	High					
Output current¹						
I _{oz}	Hi-Z state	CE1 = High or CE2 = Low, V _{OUT} = 5.5V CE1 = High or CE2 = Low, V _{OUT} = 0.5V	-15		40 -40	μA μA
I _{os}	Short circuit ³	CE1 = Low or CE2 = High, V _{OUT} = 0V, High stored				
Supply current⁴						
I _{CC}		V _{CC} = 5.25V		130	175	mA
Capacitance						
C _{IN}	Input	CE1 = High or CE2 = Low, V _{CC} = 5.0V V _{IN} = 2.0V V _{OUT} = 2.0V			5	pF
C _{OUT}	Output					

NOTES:

- Positive current is defined as into the terminal referenced.
- Typical values are at V_{CC} = 5V, T_{amb} = +25°C.
- No more than one output should be grounded at the same time and Strobe should be disabled. Strobe is in the High state.
- Measured with all inputs grounded and all outputs open.

4K-bit TTL bipolar PROM (512 × 8)

82S115

AC ELECTRICAL CHARACTERISTICS

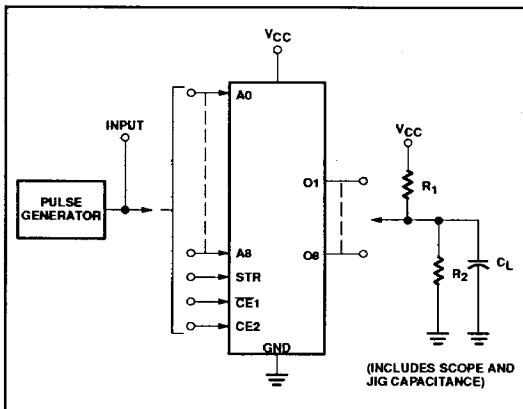
$R_1 = 470\Omega$, $R_2 = 1k\Omega$, $C_L = 30pF$, $0^\circ C \leq T_{amb} \leq +75^\circ C$, $4.75V \leq V_{CC} \leq 5.25V$

SYMBOL	PARAMETER	TO	FROM	TEST CONDITIONS	LIMITS			UNIT
					Min	Typ ²	Max	
Access time¹								
t_{AA}		Output	Address	Latched or transparent read ^{3,4}	45	60		ns
t_{CE}		Output	Chip Enable		25	40		ns
Disable time⁶								
t_{CD}		Output	Chip Disable	Latched or transparent read ^{3,4}	25	40		ns
Setup and hold time								
t_{CDS}	Setup time	Output	Chip Enable	Latched read only ^{4,5}	40			ns
t_{CDH}	Hold time	Output	Chip Enable	Latched read only ^{4,5}	10			ns
Hold time								
t_{ADH}	Hold time	Address	Strobe	Latched read only ^{4,5}		0		ns
Pulse width								
t_{SW}	Strobe			Latched read only ^{4,5}	30	15		ns
Latch time								
t_{SL}	Strobe			Latched read only ^{4,5}	60	35		ns
Delatch time⁵								
t_{DL}	Strobe			Latched read only ^{4,5}			35	ns

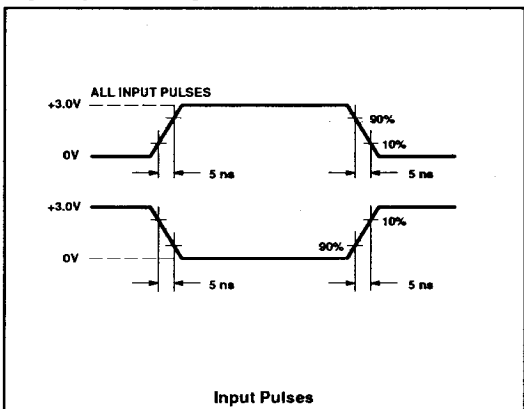
NOTES:

1. Tested at an address cycle time of 1μs.
2. Typical values are $V_{CC} = 5V$, $T_{amb} = +25^\circ C$.
3. If the Strobe is High, the device functions in a manner identical to conventional bipolar ROMs. The timing diagram shows valid data will appear t_{AA} nanoseconds after the address has changed or t_{CE} nanoseconds after the output circuit is enabled.
4. During operation the fusing pins FE1 and FE2 must be grounded or left floating.
5. In latched Read Mode data from any selected address will be held on the output when Strobe is lowered. Only when Strobe is raised will new location data be transferred and Chip Enable conditions be stored. The new data will appear on the outputs if the Chip Enable conditions enable the outputs.
6. Measured at a delta of 0.5V from Logic Level with $R_1 = 750\Omega$, $R_2 = 750\Omega$ and $C_L = 5pF$.

TEST LOAD CIRCUIT



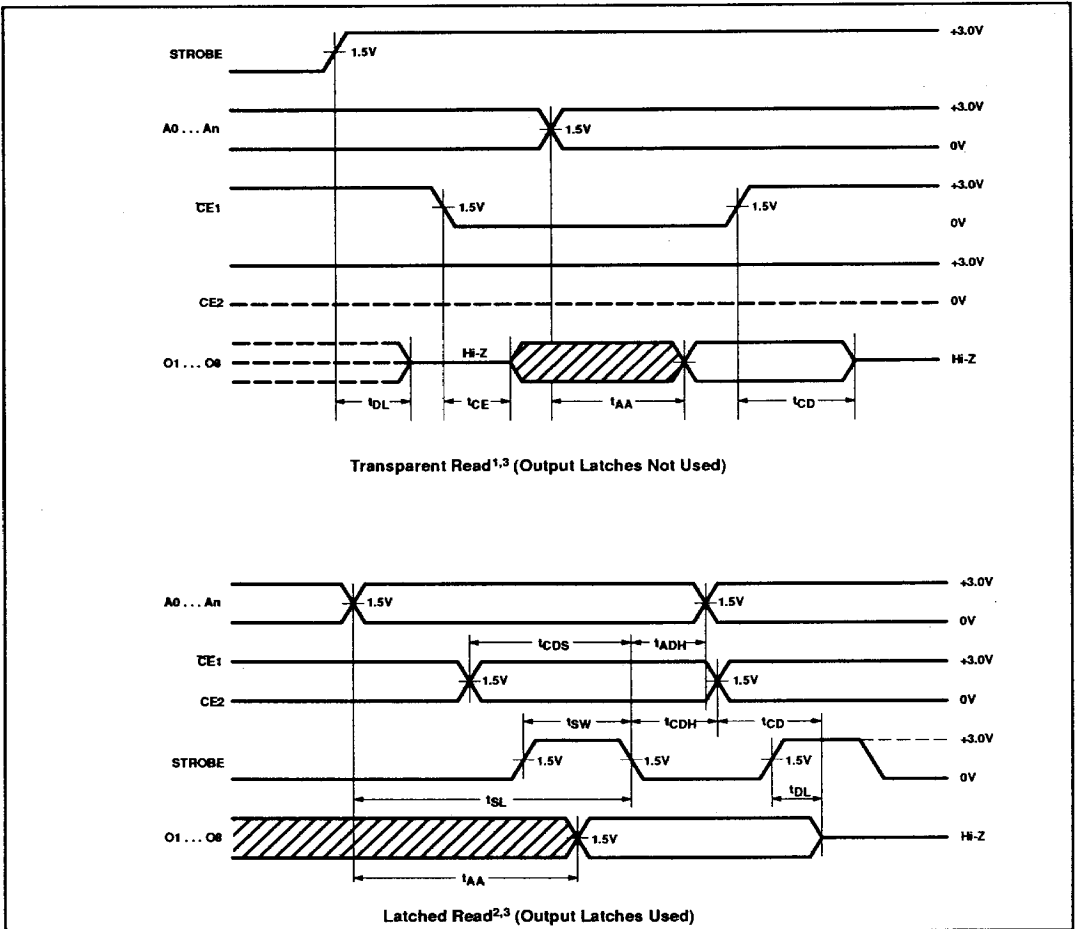
VOLTAGE WAVEFORM



4K-bit TTL bipolar PROM (512 × 8)

82S115

TIMING DIAGRAMS



NOTES:

1. If the Strobe is High, the device functions in a manner identical to conventional bipolar ROMs. The timing diagram shows valid data will appear t_{AA} nanoseconds after the address has changed or t_{CE} nanoseconds after the output circuit is enabled.
2. In Latched Read Mode data from any selected address will be held on the output when Strobe is lowered. Only when Strobe is raised will new location data be transferred and Chip Enable conditions be stored. The new data will appear on the outputs if the Chip Enable conditions enable the outputs.
3. Areas shown by crosshatch are latched data from previous address.